



BN10(2CN3,BZU1)

GLASS PASSIVATED SILICON DAMPING DIODE

Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: QZJ840611



TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications	Test Condition
Use for			Rectifier, damping circuit.	
Store temperature	T	°C	-55~+150	
Quality Class			GS	
Peak Repetitive Reverse Voltage	V _{RRM}	V	50~1400	
Average Forward Current	I _{F(AV)}	A	1.0	
Peak Forward Voltage	V _{FM}	V	A~G: 1.8 H~J: 2.5	I=A I _{F(AV)} , A=3.1415926
Average Forward Voltage	V _F	V	1.0	I=I _{F(AV)}
Non-repeat Forward Surge Current	I _{FSM}	A	30	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	I _{RM1}	uA	10	V _R =V _{RRM} , Ta=25°C
Peak Reverse Current	I _{RM2}	uA	200	V _R =V _{RRM} , Ta=125°C
Junction Temperature	T _{jm}	°C	150	
Reverse Recovery Time	t _{rr}	uS	4	V _R =10V, I _F =50mA, R _L =75ohms

SPECIFICATIONS:

A	B	C	D	E	F	G	H	I	J
50V	100V	200V	300V	400V	600V	800V	1000V	1200V	1400V

Outline and Dimensions: